



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



企业QQ二维码

Features

- $BV_{CEO} > -100V$
- $BV_{ECO} > -7V$
- $I_C = -2A$ Continuous Collector Current
- $V_{CE(SAT)} < -130mV$ @ -1A
- $R_{CE(SAT)} = 108m\Omega$ Typical
- $P_D = 1.25W$
- High Peak Current
- Complementary Part Number NK-ZXTN25100BFH

Mechanical Data

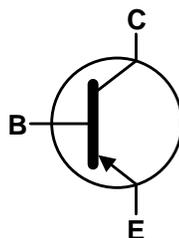
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.008 grams (Approximate)

Applications

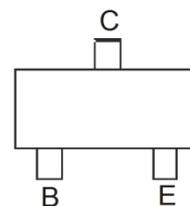
- MOSFET and IGBT Gate Driving
- DC-DC Converters
- Motor Drive
- Relay, Lamp and Solenoid Drive



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-140	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEO}	-100	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current (Note 5)	I _C	-2	A
Peak Pulse Current	I _{CM}	-5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Note 5)	P _D	0.73	W
	(Note 6)		5.84	
	(Note 7)		1.05	
			8.4	
	(Note 8)		1.25	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	9.6	°C/W
	(Note 6)		1.81	
	(Note 7)		14.5	
	(Note 8)		171	
Thermal Resistance, Junction to Lead	(Note 9)	R _{θJL}	119	°C/W
Operating and Storage Temperature Range	—	T _J , T _{STG}	100	°C
			69	
			74.95	°C/W
			-55 to +150	°C

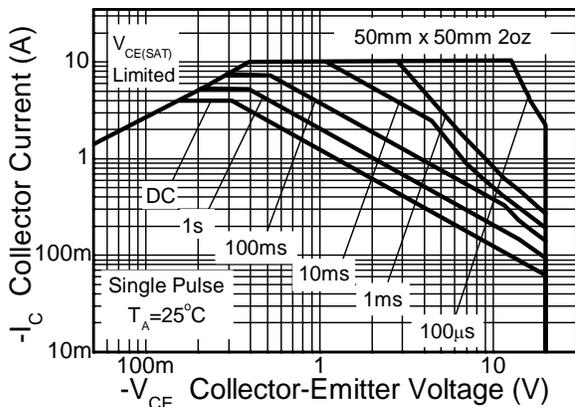
- Notes:
5. For a device surface mounted on 15mm x 15mm x 1.6mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Same as note (5), except the device is surface mounted on 25mm x 25mm with 2 oz copper.
 7. Same as note (5), except the device is surface mounted on 50mm x 50mm with 2 oz copper.
 8. Same as note (6), except the device is measured at t<5secs.
 9. Thermal resistance from junction to solder-point (at the end of the collector lead).

ESD Ratings (Note 10)

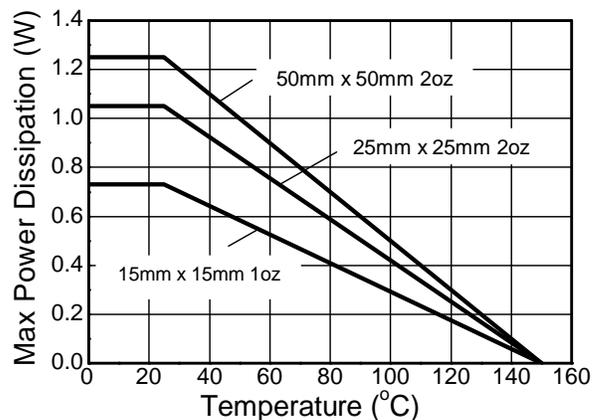
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Note: 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

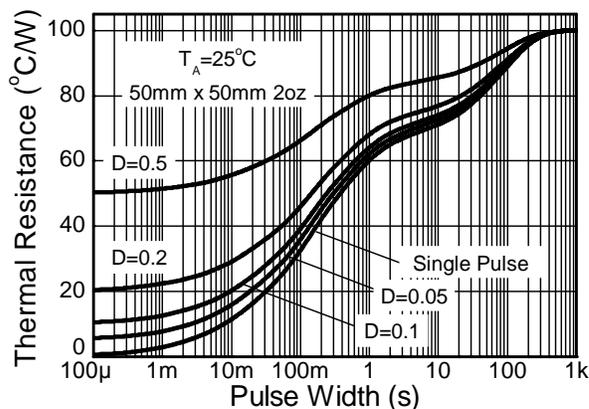
Thermal Characteristics and Derating Information



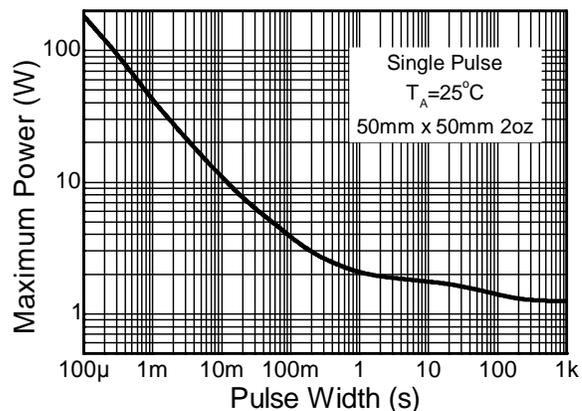
Safe Operating Area



Derating Curve



Transient Thermal Impedance



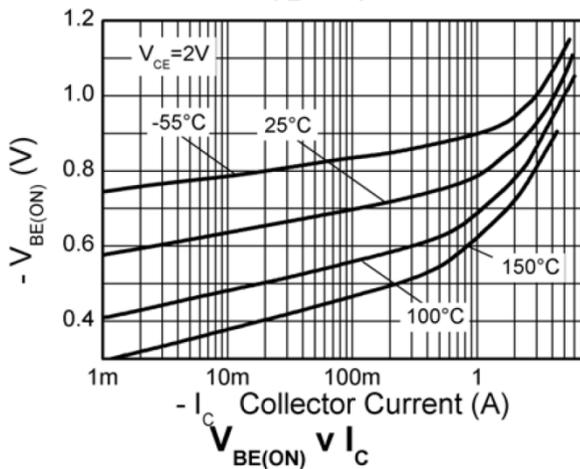
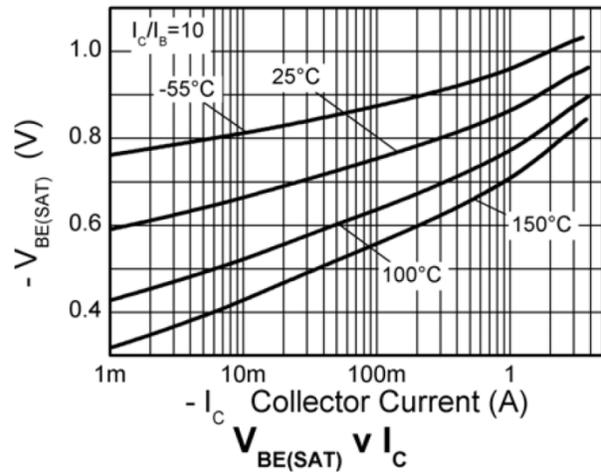
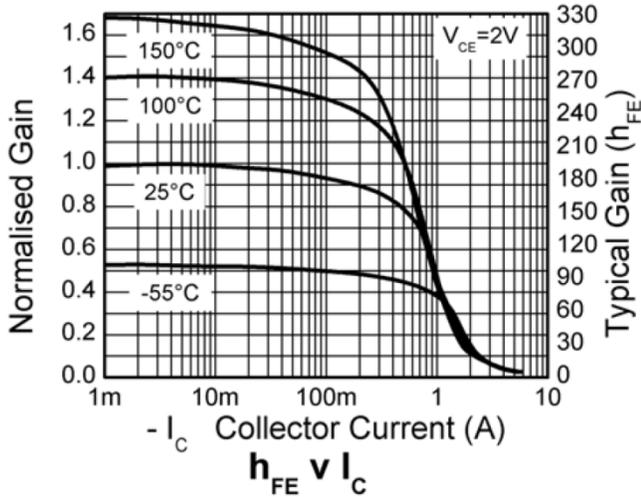
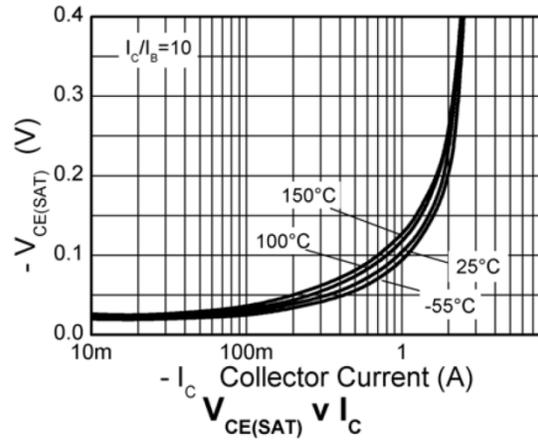
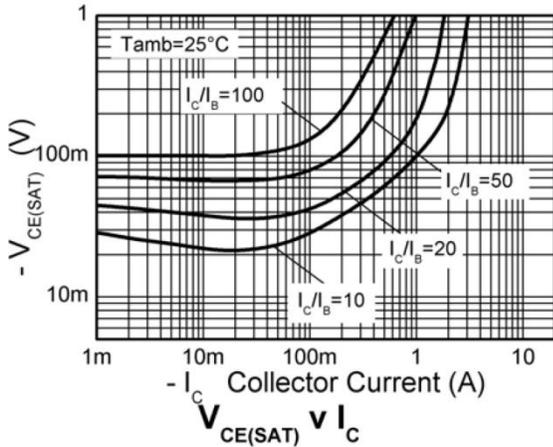
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-140	-165	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-100	-125	—	V	I _C = -10mA
Collector-Emitter Breakdown Voltage	BV _{CEX}	-140	-165	—	V	I _E = -100μA, R _{BC} < 1kΩ or -0.25 < V _{BE} < 1V
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.2	—	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}	—	< -1	-50	nA	V _{CB} = -112V
		—	—	-20	μA	V _{CB} = -112V, T _A = +100°C
Emitter-Base Cutoff Current	I _{EBO}	—	< -1	-50	nA	V _{EB} = -5.6V
Static Forward Current Transfer Ratio (Note 11)	h _{FE}	100	200	300	—	I _C = -10mA, V _{CE} = -2V
		55	105	—		I _C = -1A, V _{CE} = -2V
		15	25	—		I _C = -2A, V _{CE} = -2V
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(SAT)}	—	-60	-90	mV	I _C = -0.5A, I _B = -50mA
		—	-240	-350		I _C = -0.5A, I _B = -10mA
		—	-100	-130		I _C = -1A, I _B = -100mA
		—	-215	-295		I _C = -2A, I _B = -200mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(SAT)}	—	-900	-1000	mV	I _C = -2A, I _B = -200mA
Base-Emitter Voltage (Note 11)	V _{BE(ON)}	—	-830	-950	mV	I _C = -2A, V _{CE} = -2V
Output Capacitance	C _{OBO}	—	15	25	pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f _T	—	200	—	MHz	V _{CE} = -5V, I _C = -100mA, f = 100MHz
Turn-on Time	t _(ON)	—	31	—	ns	V _{CC} = -10V, I _C = -500mA,
Turn-off Time	t _(OFF)	—	384	—	ns	I _{B1} = -I _{B2} = -50mA

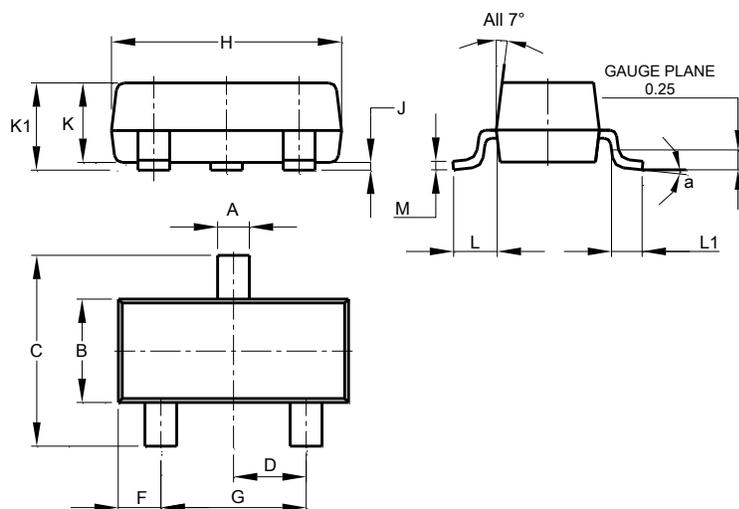
Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Package Outline Dimensions

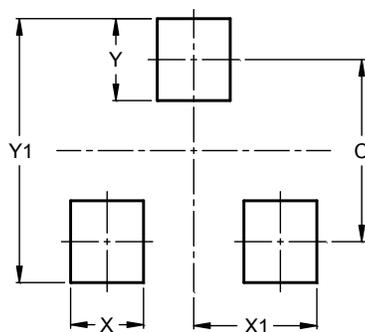
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9